

ABSTRACT OF THE DISCLOSURE

A semiconductor laser has a first cladding layer (2) of a first conductivity type, an active layer (3), and a second cladding layer (4) of a second conductivity type, which are successively deposited on a semiconductor substrate (1) by epitaxial growth. The first cladding layer (2) and/or the second cladding layer (4) is made of a compound semiconductor material of a zincblende crystal structure containing Mg.

(Fig. 2)

This Sheet Has Been Replaced

